



16N65K-MT

Preliminary

Power MOSFET

16A, 650V N-CHANNEL POWER MOSFET

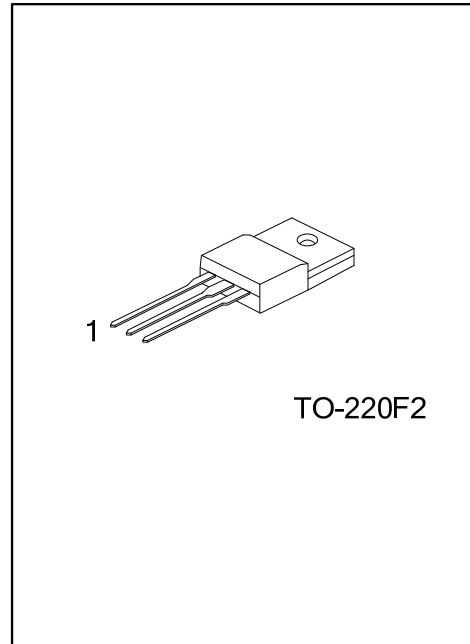
DESCRIPTION

The UTC **16N65K-MT** is an N-channel mode power MOSFET using UTC's advanced technology to provide customers with planar stripe and DMOS technology. This technology allows a minimum on-state resistance and superior switching performance. It also can withstand high energy pulse in the avalanche and commutation mode.

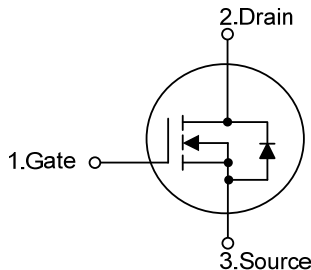
The UTC **16N65K-MT** is generally applied in high efficiency switch mode power supplies, active power factor correction and electronic lamp ballasts based on half bridge topology.

FEATURES

- * $R_{DS(ON)} < 0.54\Omega @ V_{GS} = 10V, I_D = 8A$
- * High Switching Speed
- * 100% Avalanche Tested



SYMBOL



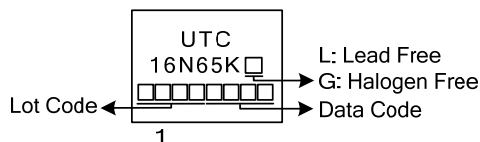
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
16N65KL-TF2-T	16N65KG-TF2-T	TO-220F2	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>16N65KL-TF2-T</p> <p>(1)Packing Type (2)Package Type (3)Green Package</p>	<p>(1) T: Tube (2) TF2: TO-220F2 (3) L: Lead Free, G: Halogen Free and Lead Free</p>
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MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_C=25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	650	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current	Continuous ($T_C=25^\circ\text{C}$)	I_D	16 (Note 2)	A
	Pulsed (Note 3)	I_{DM}	64 (Note 2)	A
Avalanche Current (Note 3)		I_{AR}	16	A
Avalanche Energy	Single Pulsed (Note 4)	E_{AS}	780	mJ
	Repetitive (Note 5)	E_{AR}	20	mJ
Peak Diode Recovery dv/dt (Note 5)		dv/dt	4.5	V/ns
Power Dissipation ($T_C=25^\circ\text{C}$)		P_D	62	W
Linear Derating Factor above $T_C=25^\circ\text{C}$			0.49	W/ $^\circ\text{C}$
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55~+150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Drain current limited by maximum junction temperature
3. Repetitive Rating: Pulse width limited by maximum junction temperature
4. $L = 6.1\text{mH}$, $I_{AS} = 16\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
5. $I_{SD} \leq 16\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
Junction to Case	θ_{JC}	2.0	$^\circ\text{C}/\text{W}$

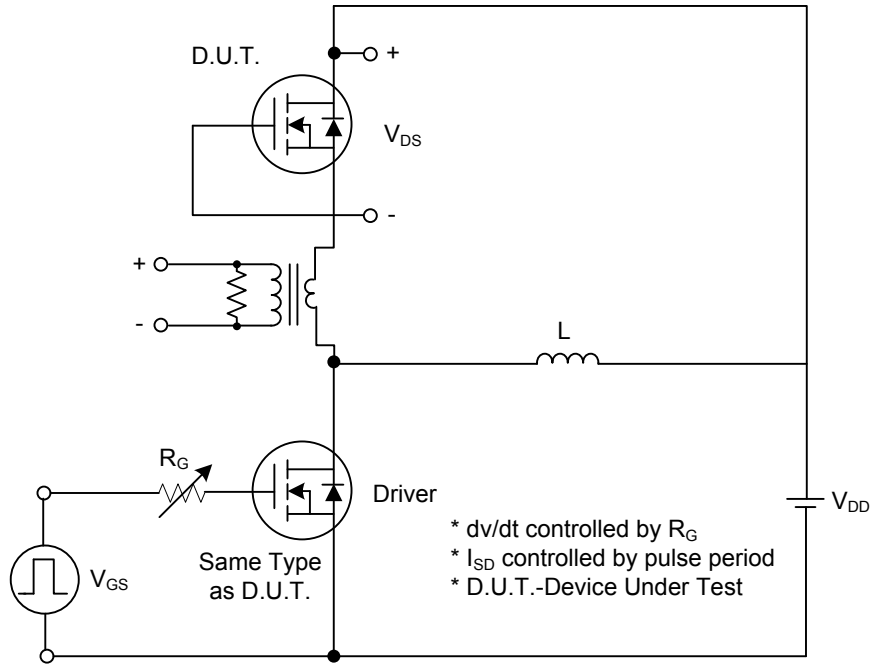
■ ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	650			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=650\text{V}$, $V_{GS}=0\text{V}$			1	μA
		$V_{DS}=520\text{V}$, $V_{GS}=0\text{V}$, $T_C=125^\circ\text{C}$			10	μA
Gate- Source Leakage Current	Forward	I_{GSS}				+100
	Reverse					$V_{GS}=+30\text{V}$, $V_{DS}=0\text{V}$
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	2.0		4.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10\text{V}$, $I_D=8\text{A}$		0.35	0.54	Ω
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	$V_{GS}=0\text{V}$, $V_{DS}=25\text{V}$, $f=1.0\text{MHz}$		1078		pF
Output Capacitance	C_{OSS}			225		pF
Reverse Transfer Capacitance	C_{RSS}			10		pF
SWITCHING PARAMETERS						
Turn-ON Delay Time	$t_{D(ON)}$	$V_{DS}=30\text{V}$, $I_D=0.5\text{A}$, $R_G=25\Omega$ (Note 1, 2)		112		ns
Rise Time	t_R			186		ns
Turn-OFF Delay Time	$t_{D(OFF)}$			335		ns
Fall-Time	t_F			186		ns
Total Gate Charge	Q_G	$V_{GS}=10\text{V}$, $V_{DS}=50\text{V}$, $I_D=1.3\text{A}$ (Note 1, 2)		57		nC
Gate to Source Charge	Q_{GS}			15.4		nC
Gate to Drain Charge	Q_{GD}			15.8		nC
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Body-Diode Continuous Current	I_S				16	A
Maximum Body-Diode Pulsed Current	I_{SM}				64	A
Drain-Source Diode Forward Voltage	V_{SD}	$I_S=16\text{A}$, $V_{GS}=0\text{V}$			1.4	V

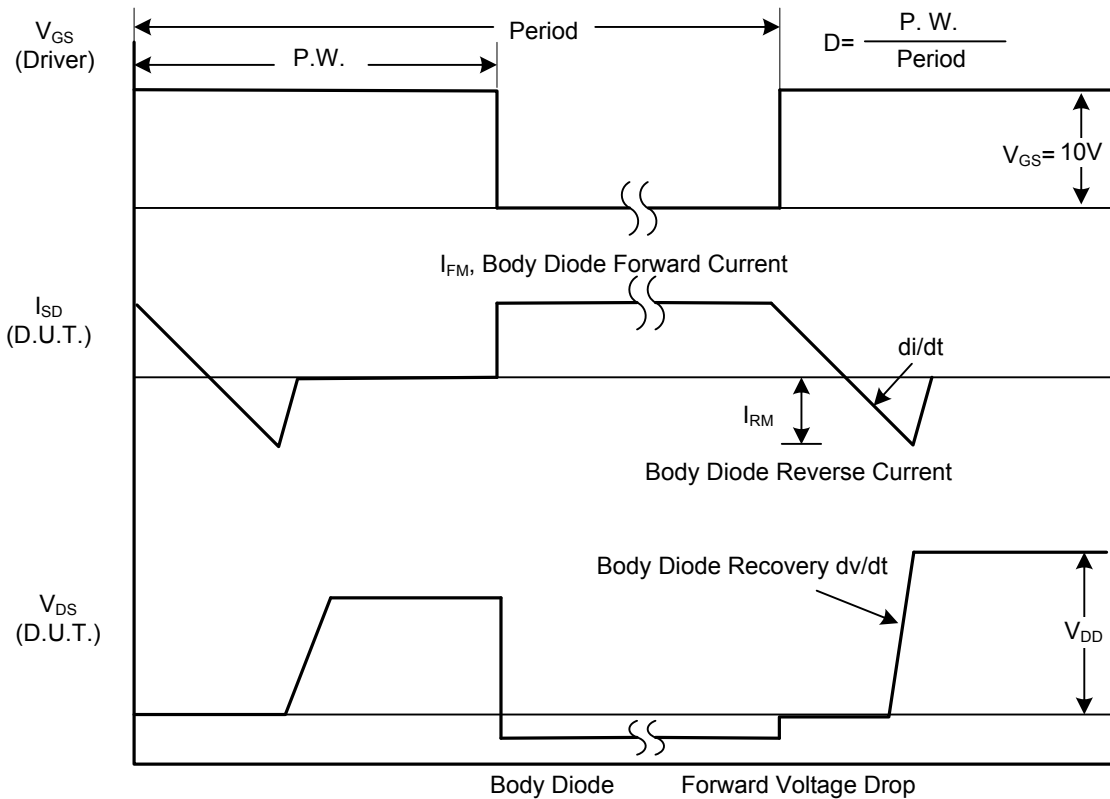
Notes: 1. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$

2. Essentially independent of operating temperature

■ TEST CIRCUITS AND WAVEFORMS

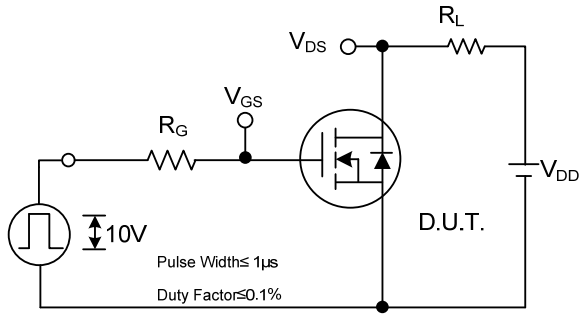


Peak Diode Recovery dv/dt Test Circuit

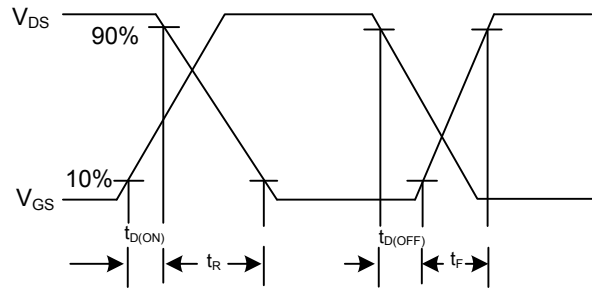


Peak Diode Recovery dv/dt Waveforms

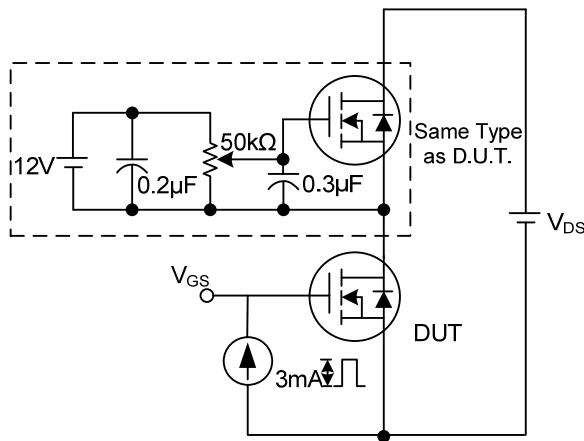
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



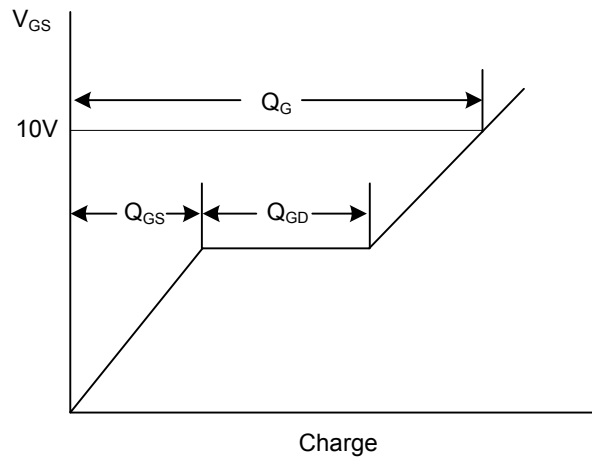
Switching Test Circuit



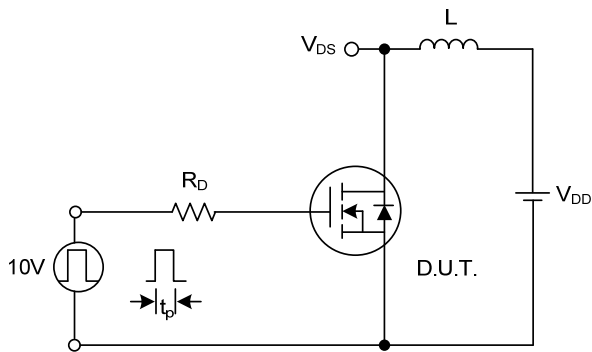
Switching Waveforms



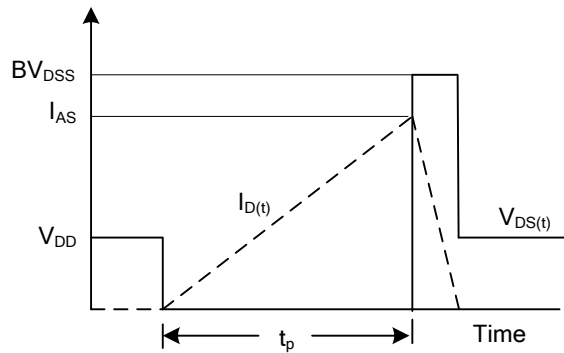
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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